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TSMC-02-350



April 30, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/757,202 01/14/04 |

Tung-Ching Tseng et al.

METHOD FOR CHEMICAL MECHANICAL
POLISHING OF A SHALLOW TRENCH
ISOLATION STRUCTURE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on May 4, 2004.

Stephen B. Ackerman, Reg.# 37761

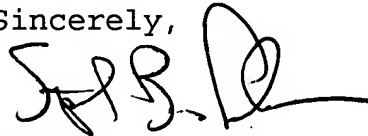
Signature/Date

Spw *SB* *5/4/04*

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U.S. Patent Application Publication US 2002/0110995 A1 to Kim, "Use of Discrete Chemical Mechanical Polishing Processes to Form a Trench Isolation Region," discloses a method of forming a trench isolation region using discrete chemical mechanical polishing processes.

Sincerely,

A handwritten signature in black ink, appearing to read "S.B. Ackerman", with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

